[redacted]

[redacted]	[redacted]	[redacted]	**Unit**
[redacted]to[redacted]age junction temperature range	T_{stg}	-40-150	Ņ
[redacted]p[redacted]rating junction temperature range	T_j	-40-125	Ņ
Re[redacted]etitive peak off-state voltage (T_j=25Ņ)	V_{DRM}	1000	V
Re[redacted]etitive peak reverse voltage (T_j=25Ņ)	V_{RRM}	1000	V
RM[redacted]S on-state current (T_C Ů 104Ņ)	$I_{T(RMS)}$	4	A
No[redacted] repetitive surge peak on-state current (fu[redacted] cycle , t_p=20ms , T_j=25Ņ)	I_{TSM}	40	A
No[redacted] repetitive surge peak on-state current (fu[redacted] cycle , t_p=16.6ms , T_j=25Ņ)		44	
I^2t [redacted]value for fusing (t_p=10ms , T_j=25Ņ)	I^2t	8	A^2s
Cr[redacted]tical rate of rise of on-state current (I_G[redacted]=2 ¦ I_{GT} , f=100Hz , T_j=125Ņ)	dI/dt	100	A/μs
Pe[redacted]ak gate current (t_p=20μs , T_j=125Ņ)	I_{GM}	4	A

Average gate power dissipation (T_j=125Ņ) P

AC J T 04 F -1000 CW

AC switch

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Triacs

$I_{T(RMS)}$:4A

F:TO-220F(Ins)

CW: I_{GT1-3} Ů 35mA

1000:V_{DRM} /V_{RRM} ů 1000V

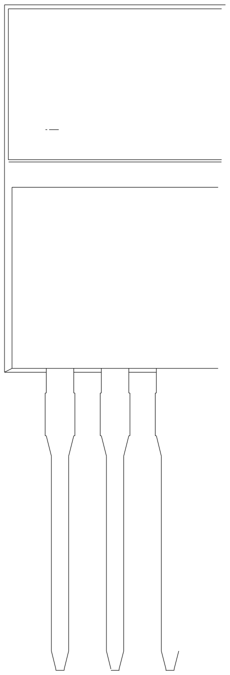

FIG.1: Maximum power dissipation versus RMS on-state current

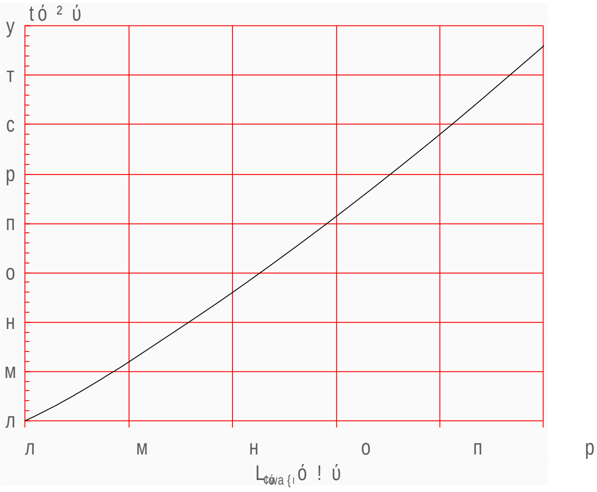

FIG.2: RMS on-state current versus case temperature

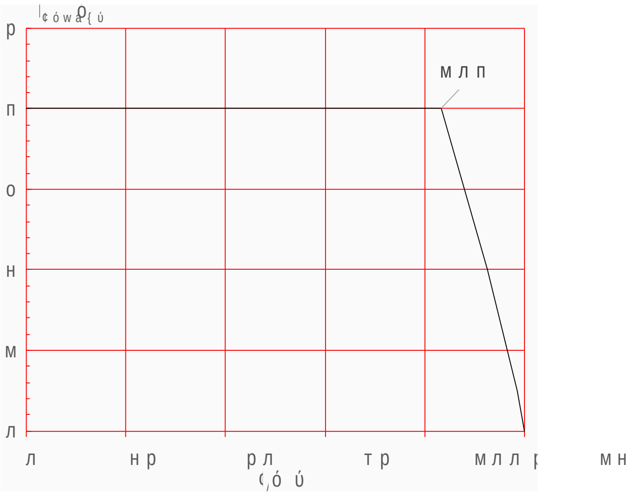

FIG.3: Surge peak on-state current versus number of cycles

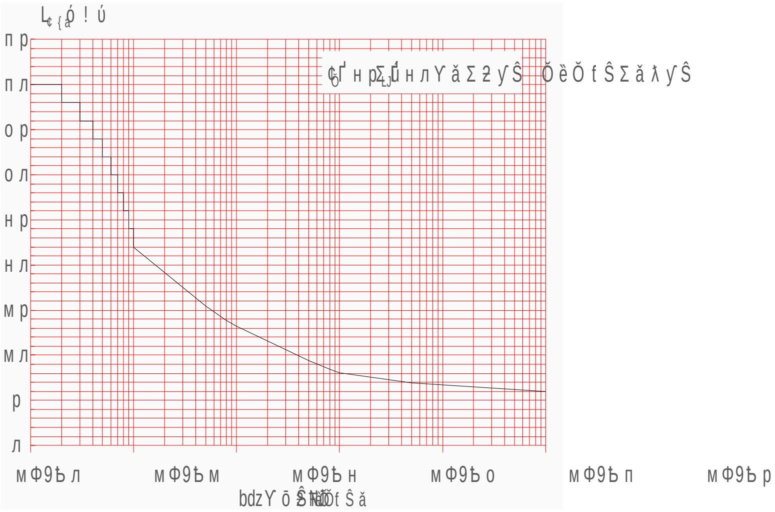

FIG.4: On-state characteristics

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